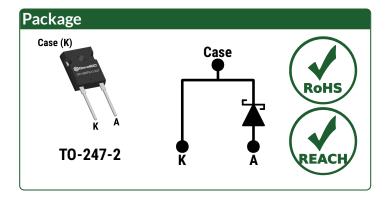
### Silicon Carbide Schottky Diode



 $V_{RRM}$  = 1200 V  $I_{F(T_C = 153^{\circ}C)}$  = 15 A  $Q_C$  = 80 nC

#### **Features**

- Low V<sub>F</sub> for High Temperature Operation
- Enhanced Surge and Avalanche Robustness
- Superior Figure of Merit Qc/IF
- Low Thermal Resistance
- Low Reverse Leakage Current
- Temperature Independent Fast Switching
- Positive Temperature Coefficient of V<sub>F</sub>
- High dV/dt Ruggedness



### **Advantages**

- Improved System Efficiency
- High System Reliability
- Optimal Price Performance
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- Easy to Parallel without Thermal Runaway
- Enables Extremely Fast Switching

#### **Applications**

- Power Factor Correction (PFC)
- Electric Vehicles and Battery Chargers
- Solar Inverters
- High Frequency Converters
- Switched Mode Power Supply (SMPS)
- Motor Drives
- Anti-Parallel / Free-Wheeling Diode
- · LED and HID Lighting

Absolute Maximum Ratings (At T <sub>C</sub> = 25°C Unless Otherwise Stated)								
Parameter	Symbol	Conditions	Values	Unit	Note			
Repetitive Peak Reverse Voltage	$V_{RRM}$		1200	٧				
	I <sub>F</sub>	T <sub>C</sub> = 100°C, D = 1	32					
Continuous Forward Current		$T_C = 135^{\circ}C$ , D = 1	22	Α	Fig. 4			
		$T_C = 153^{\circ}C$ , D = 1	15					
Non-Repetitive Peak Forward Surge Current, Half Sine Wave	I <sub>F,SM</sub>	$T_C$ = 25°C, $t_P$ = 10 ms	5°C, t <sub>P</sub> = 10 ms 150					
		$T_C$ = 150°C, $t_P$ = 10 ms	120	Α				
Repetitive Peak Forward Surge Current, Half Sine Wave	I <sub>F,RM</sub>	$T_C$ = 25°C, $t_P$ = 10 ms	90	۸				
		$T_C$ = 150°C, $t_P$ = 10 ms	63	Α				
Non-Repetitive Peak Forward Surge Current	I <sub>F,MAX</sub>	$T_C$ = 25°C, $t_P$ = 10 $\mu$ s	750	Α				
i <sup>2</sup> t Value	∫i²dt	$T_C$ = 25°C, $t_P$ = 10 ms	112	A <sup>2</sup> s				
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	L = 2.4 mH, I <sub>AS</sub> = 15 A	270	mJ				
Diode Ruggedness	dV/dt	V <sub>R</sub> = 0 ~ 960 V	200	V/ns				
Power Dissipation	P <sub>TOT</sub>	T <sub>C</sub> = 25°C	199	W	Fig. 3			
Operating and Storage Temperature	Tj, Tstg		-55 to 175	°C				



<b>Electrical Characteristics</b>								
Parameter	Symbol	Conditions -		Values			Unit	Note
	Зуший			Min.	Тур.	Max.	Ullit	Note
Diode Forward Voltage	$V_F$	I <sub>F</sub> = 15 A, T <sub>j</sub> = 25°C			1.5	1.8	٧	Fig. 1
	VF	I <sub>F</sub> = 15 A, T <sub>j</sub> = 175°C			1.9			
Reverse Current	l <sub>n</sub>	V <sub>R</sub> = 1200 V, T <sub>j</sub> = 25°C			2	10	μΑ	Fig. 2
	IR	$V_R = 1200 \text{ V, } T_j = 175^{\circ}\text{C}$			17			
Total Capacitive Charge	Qc		$V_R = 400 V$		55		nC	Fig. 7
	QU	_ l <sub>F</sub> ≤ l <sub>F,MAX</sub> dl <sub>F</sub> /dt = 200 A/µs	$V_{R} = 800 V$		80		110	
Switching Time	t <sub>o</sub>		$V_{R} = 400 \text{ V}$		< 10		ns	
	ts		$V_{R} = 800 V$		<b>\ 10</b>		115	
Total Capacitance	С	V <sub>R</sub> = 1 V, f = 1MHz			914		ьE	Fig. 6
		$V_R = 800 \text{ V, } f = 1 \text{MHz}$			53		pF	

Thermal/Package Characteristics							
Parameter	Symbol	Conditions	Values			Heit	Note
		Conditions	Min.	Тур.	Max.	Unit	Note
Thermal Resistance, Junction - Case	$R_{thJC}$			0.75		°C/W	Fig. 9
Weight	W <sub>T</sub>			6.0		g	
Mounting Torque	T <sub>M</sub>	Screws to Heatsink			1.1	Nm	





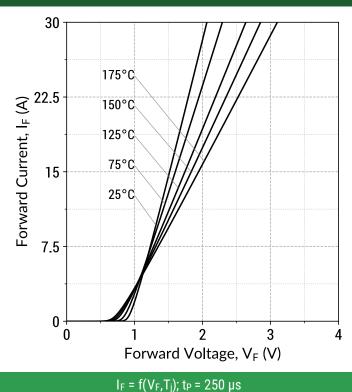
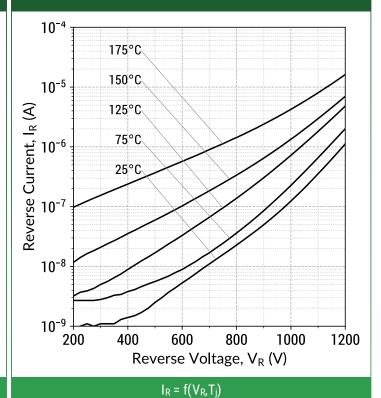


Figure 2: Typical Reverse Characteristics



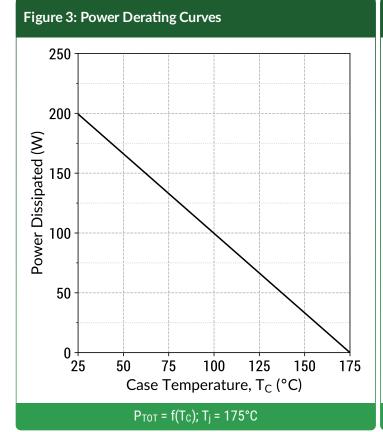
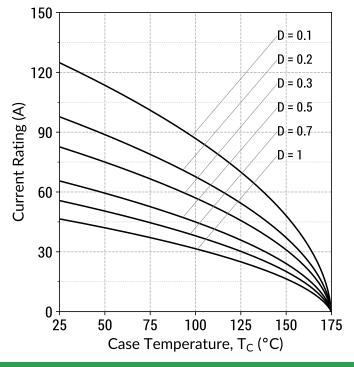


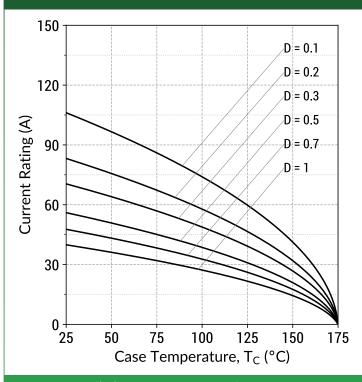
Figure 4: Current Derating Curves (Typical V<sub>F</sub>)



 $I_F = f(T_C); D = t_P/T; T_j \le 175^{\circ}C; f_{SW} > 10kHz$ 

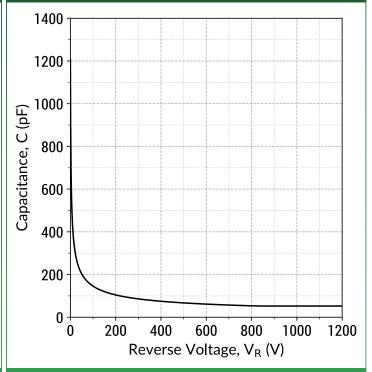


Figure 5: Current Derating Curves (Maximum V<sub>F</sub>)



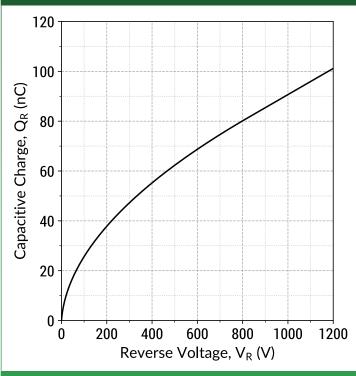
 $I_F = f(T_C); D = t_P/T; T_j \le 175^{\circ}C; f_{SW} > 10kHz$ 

Figure 6: Typical Junction Capacitance vs Reverse Voltage Characteristics



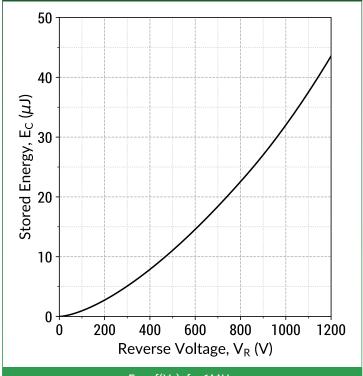
 $C = f(V_R)$ ; f = 1MHz

Figure 7: Typical Capacitive Charge vs Reverse Voltage Characteristics



 $Q_C = f(V_R)$ ; f = 1MHz

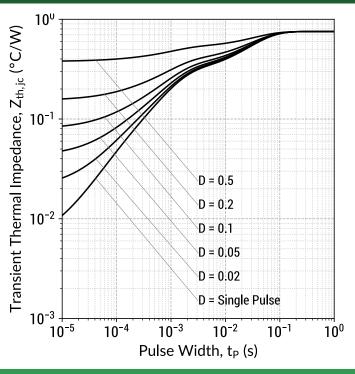
Figure 8: Typical Capacitive Energy vs Reverse Voltage Characteristics



 $E_C = f(V_R)$ ; f = 1MHz

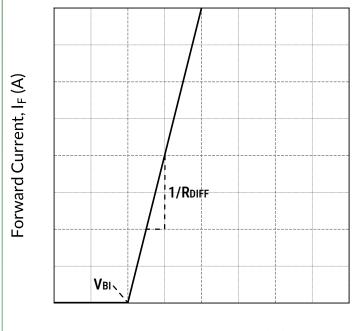


Figure 9: Transient Thermal Impedance



 $Z_{th,jc} = f(t_P,D); D = t_P/T$ 

Figure 10: Forward Curve Model



Forward Voltage,  $V_F(V)$ 

 $I_F = f(V_F, T_j)$ 

### Forward Curve Model Equation:

 $I_F = (V_F - V_{BI})/R_{DIFF} (A)$ 

### Built-In Voltage (V<sub>BI</sub>):

$$V_{BI}(T_j) = m \times T_j + n (V)$$
  
 $m = -0.00123 (V/^{\circ}C)$   
 $n = 0.995 (V)$ 

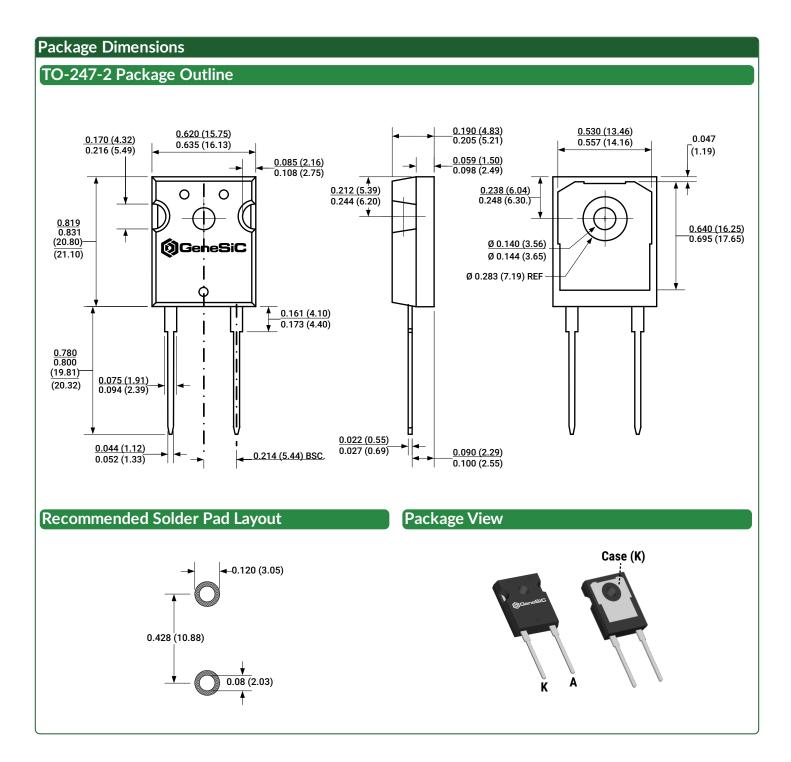
### Differential Resistance (RDIFF):

$$R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c (\Omega)$$
  
 $a = 7.95e-07 (\Omega/^{\circ}C^2)$   
 $b = 0.000113 (\Omega/^{\circ}C)$   
 $c = 0.0334 (\Omega)$ 

### **Forward Power Loss Equation:**

$$P_{LOSS} = V_{BI}(T_i) \times I_{AVG} + R_{DIFF}(T_i) \times I_{RMS}^2$$





#### **NOTE**

- 1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
- 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.





#### **Compliance**

#### **RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

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#### **Revision History**

Rev 21/Jul: Updated with most recent test data
 Supersedes: Rev 19/Apr, Rev 20/Apr, Rev 20/Apr



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